

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1.-2. (Cancelled)

3. (Original) A method for manufacturing a semiconductor device, comprising the steps of:

forming a recess in an insulating film on a substrate;

depositing a first conductive film in contact with ~~on~~ a bottom and side wall surface of the recess, the first conductive film ~~being formed from~~ comprising a first copper alloy including at least one of Al, Si, Ir or Ru having oxidation resistance;

~~growing forming~~ a second conductive film on the first conductive film by an electroplating method so as to completely fill the recess, the second conductive film comprising being formed from copper ~~or a second copper alloy~~; and

integrating the first and second conductive films into a third conductive film so as to form an embedded wiring of ~~a~~ the third conductive film.

4. (Original) The method according to claim 3, wherein the step of depositing the first conductive film includes the step of depositing the first conductive film with (111) orientation with respect to the bottom of the recess.

5. (Cancelled)

6. (New) The method according to claim 3, wherein the second conductive film comprises a copper alloy.

7. (New) The method according to claim 3, wherein the insulating film includes carbon.

8. (New) The method according to claim 3, wherein the first copper alloy includes substantially 1%, by mass, of Al.